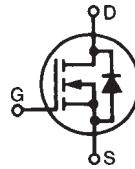
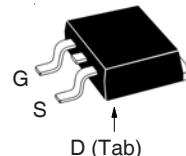
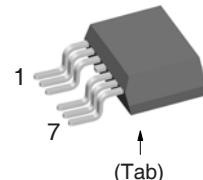


TrenchT4™
Power MOSFET
IXTA270N04T4
IXTA270N04T4-7
 $V_{DSS} = 40V$
 $I_{D25} = 270A$
 $R_{DS(on)} \leq 2.2m\Omega$
N-Channel Enhancement Mode
Avalanche Rated


TO-263 AA


 G = Gate D = Drain
 S = Source Tab = Drain

TO-263 (7-Leads)


 Pins: 1 - Gate
 2, 3, 5 , 6 , 7 - Source
 4 (Tab) - Drain

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ C$ to $175^\circ C$	40	V
V_{DGR}	$T_J = 25^\circ C$ to $175^\circ C$, $R_{GS} = 1M\Omega$	40	V
V_{GSM}	Transient	± 15	V
I_{D25}	$T_c = 25^\circ C$	270	A
I_{LRMS}	Lead Current Limit, RMS	160	A
I_{DM}	$T_c = 25^\circ C$, Pulse Width Limited by T_{JM}	800	A
I_A	$T_c = 25^\circ C$	135	A
E_{AS}	$T_c = 25^\circ C$	750	mJ
I_A	$T_c = 25^\circ C$	270	A
E_{AS}	$T_c = 25^\circ C$	350	mJ
P_D	$T_c = 25^\circ C$	375	W
T_J		-55 ... +175	$^\circ C$
T_{JM}		175	$^\circ C$
T_{stg}		-55 ... +175	$^\circ C$
T_L	Maximum Lead Temperature for Soldering	300	$^\circ C$
T_{SOLD}	1.6 mm (0.062in.) from Case for 10s	260	$^\circ C$
F_c	Mounting Force (TO-263)	10.65 / 2.2..14.6	N/lb
Weight	TO-263	2.5	g
	TO-263 (7Leads)	3.0	g

Features

- International Standard Packages
- $175^\circ C$ Operating Temperature
- High Current Handling Capability
- Avalanche Rated
- Low $R_{DS(on)}$

Advantages

- Easy to Mount
- Space Savings
- High Power Density

Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
($T_J = 25^\circ C$ Unless Otherwise Specified)				
BV_{DSS}	$V_{GS} = 0V$, $I_D = 250\mu A$	40		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	2.0		4.0 V
I_{GSS}	$V_{GS} = \pm 15V$, $V_{DS} = 0V$			± 200 nA
I_{DSS}	$V_{DS} = V_{DSS}$, $V_{GS} = 0V$			5 μA
		$T_J = 150^\circ C$		750 μA
$R_{DS(on)}$	$V_{GS} = 10V$, $I_D = 50A$, Note 1			2.2 m Ω

Applications

- Synchronous Buck Converters
- High Current Switching Power Supplies
- Battery Powered Electric Motors
- Resonant-Mode Power Supplies
- Electronics Ballast Application
- Class D Audio Amplifiers

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 10\text{V}$, $I_D = 60\text{A}$, Note 1	90	150	S
R_{GI}	Gate Input Resistance		1.4	Ω
C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$	9140	pF	
C_{oss}		1450	pF	
C_{rss}		980	pF	
$t_{d(on)}$	Resistive Switching Times $V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 135\text{A}$ $R_G = 2\Omega$ (External)	18	ns	
t_r		28	ns	
$t_{d(off)}$		72	ns	
t_f		23	ns	
$Q_{g(on)}$	$V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{D25}$	182	nC	
Q_{gs}		45	nC	
Q_{gd}		67	nC	
R_{thJC}			0.40	$^\circ\text{C}/\text{W}$

Source-Drain Diode

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
I_s	$V_{GS} = 0\text{V}$		270	A
I_{SM}	Repetitive, Pulse width limited by T_{JM}		1080	A
V_{SD}	$I_F = 100\text{A}$, $V_{GS} = 0\text{V}$, Note 1		1.4	V
t_{rr}	$I_F = 150\text{A}$, $V_{GS} = 0\text{V}$ $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 30\text{V}$	48	ns	
I_{RM}		1.8	A	
Q_{RM}		43	nC	

- Notes:
1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.
 2. On through-hole packages, $R_{DS(on)}$ Kelvin test contact location must be 5mm or less from the package body.

PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

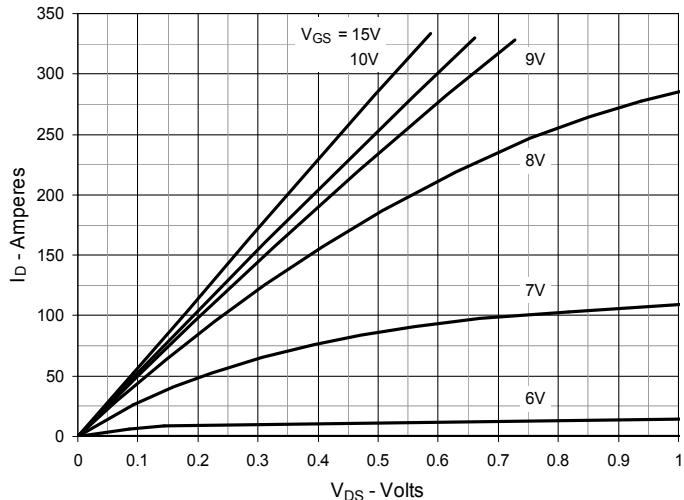
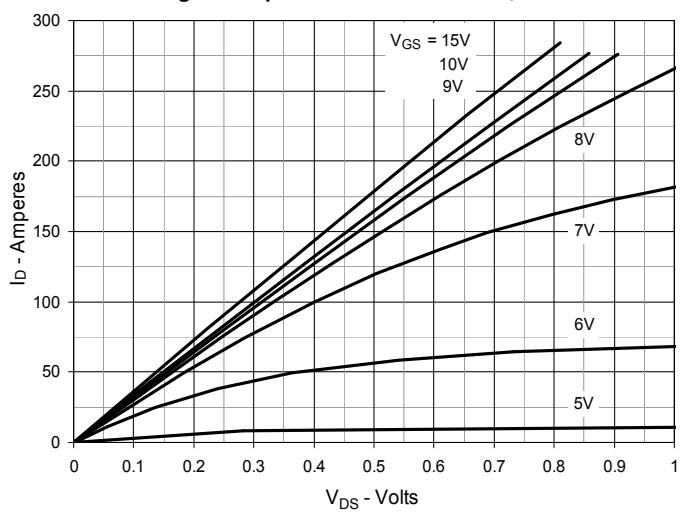
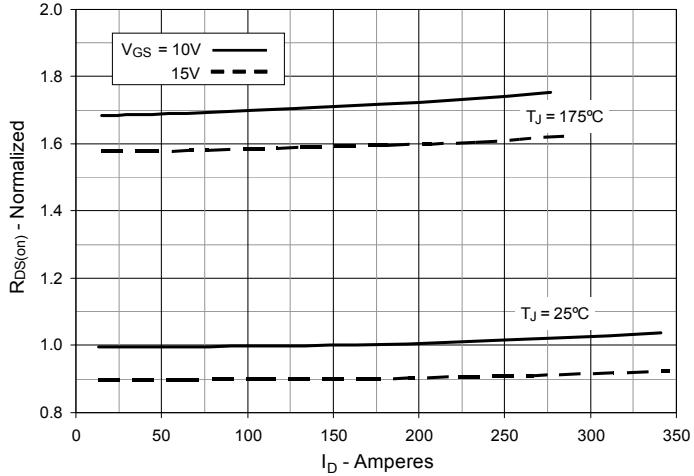
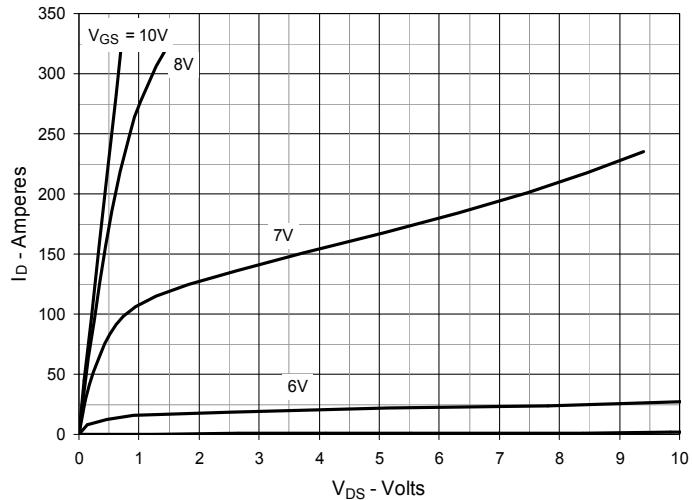
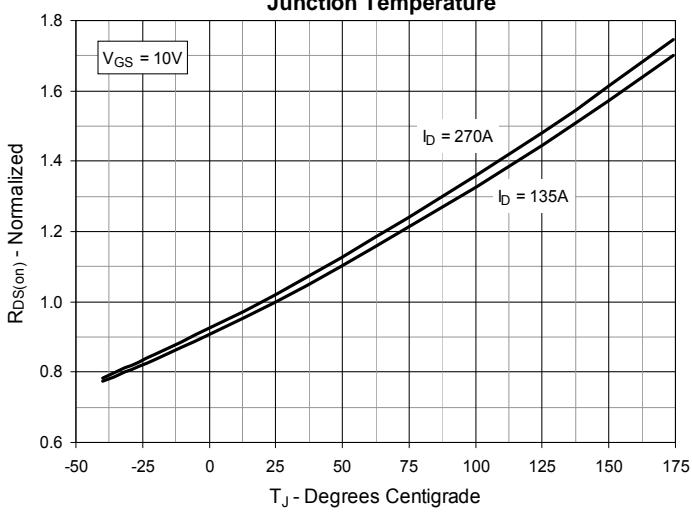
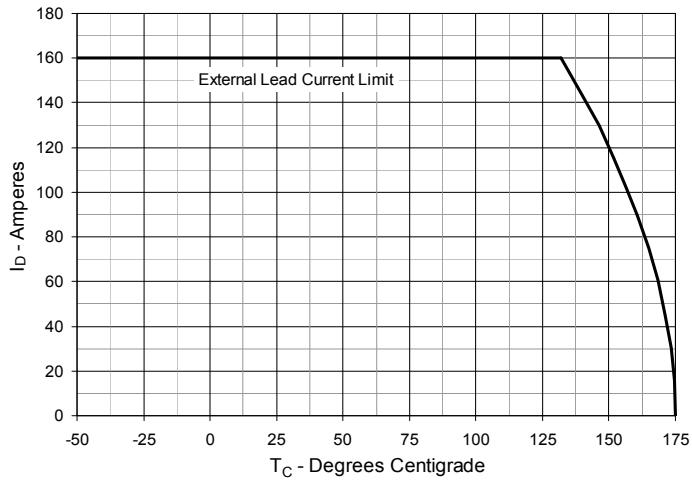
Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 3. Output Characteristics @ $T_J = 150^\circ\text{C}$

Fig. 5. Normalized $R_{DS(on)}$ to $I_D = 135\text{A}$ vs. Drain Current

Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 4. Normalized $R_{DS(on)}$ to $I_D = 135\text{A}$ Value vs. Junction Temperature

Fig. 6. Drain Current vs. Case Temperature


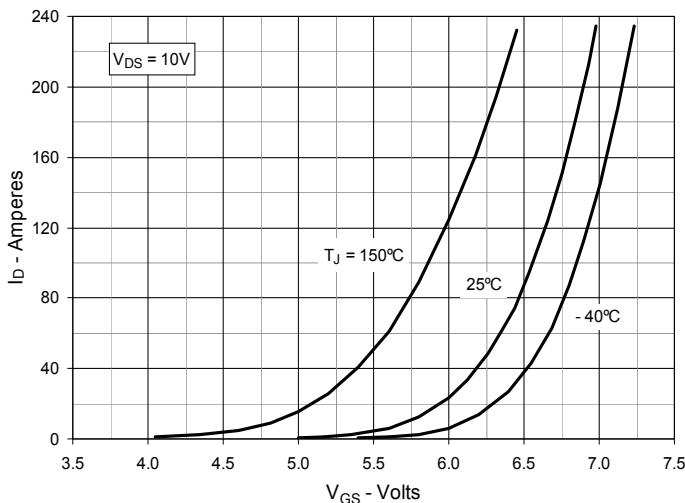
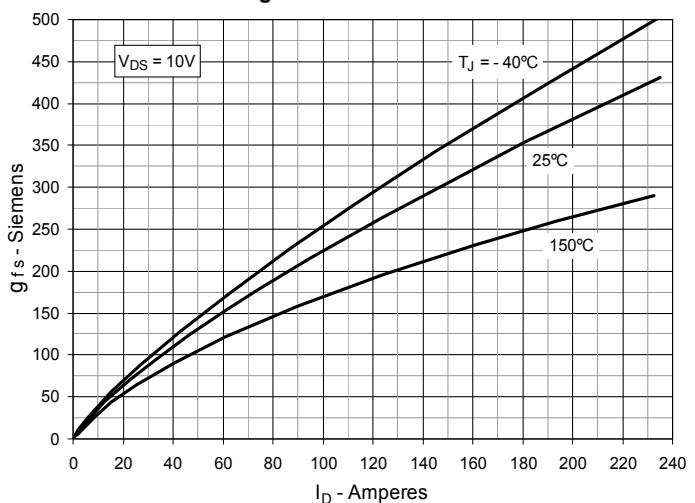
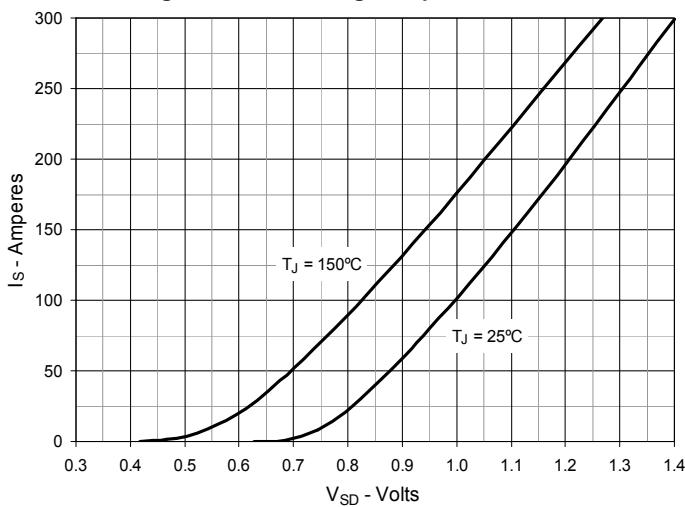
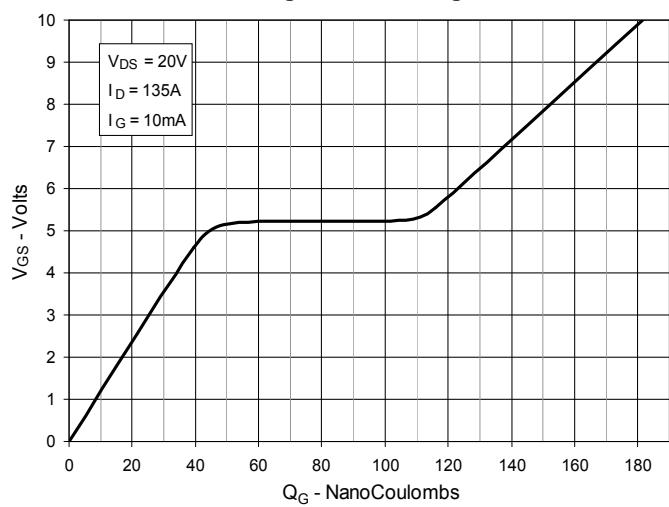
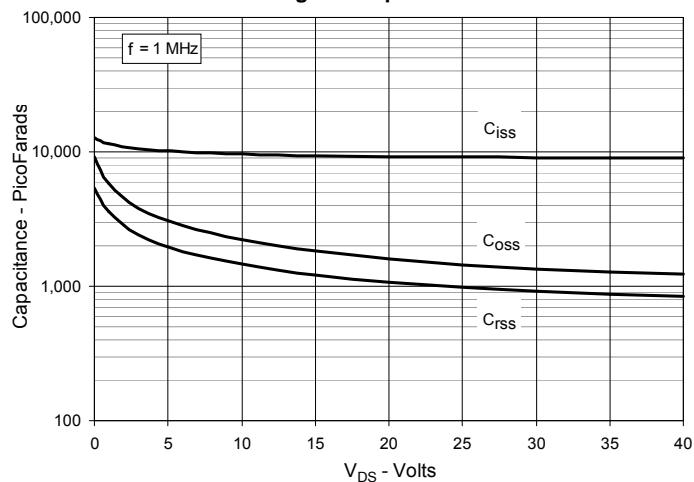
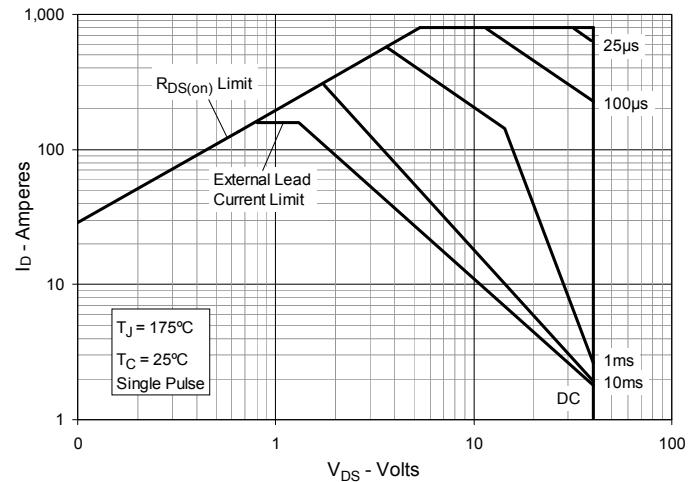
Fig. 7. Input Admittance

Fig. 8. Transconductance

Fig. 9. Forward Voltage Drop of Intrinsic Diode

Fig. 10. Gate Charge

Fig. 11. Capacitance

Fig. 12. Forward-Bias Safe Operating Area


Fig. 13. Resistive Turn-on Rise Time vs. Junction Temperature

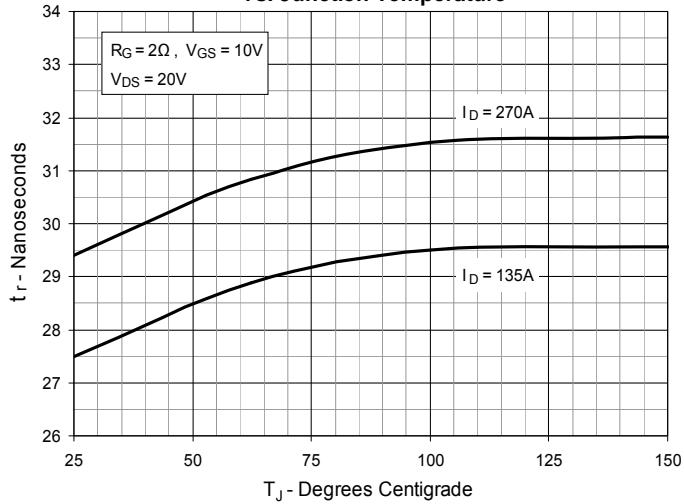


Fig. 14. Resistive Turn-on Rise Time vs. Drain Current

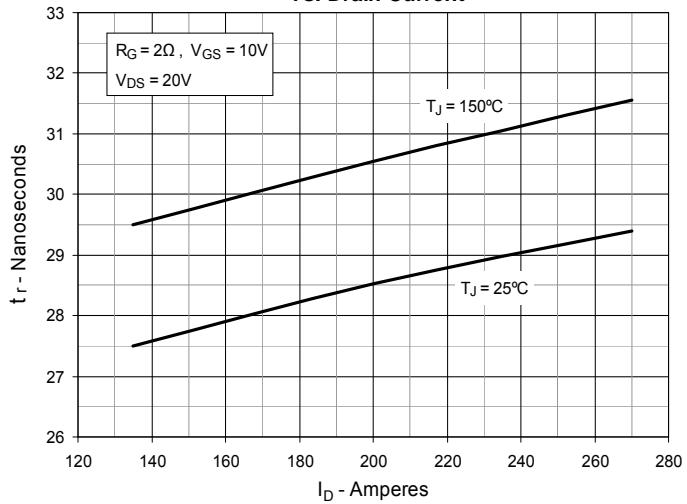


Fig. 15. Resistive Turn-on Switching Times vs. Gate Resistance

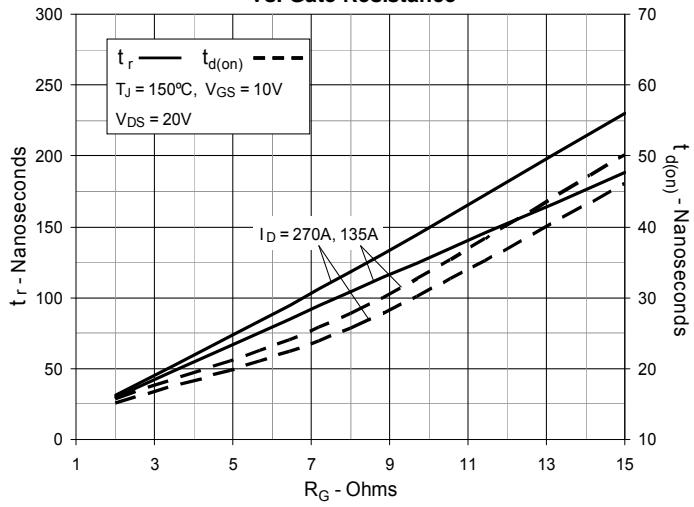


Fig. 16. Resistive Turn-off Switching Times vs. Junction Temperature

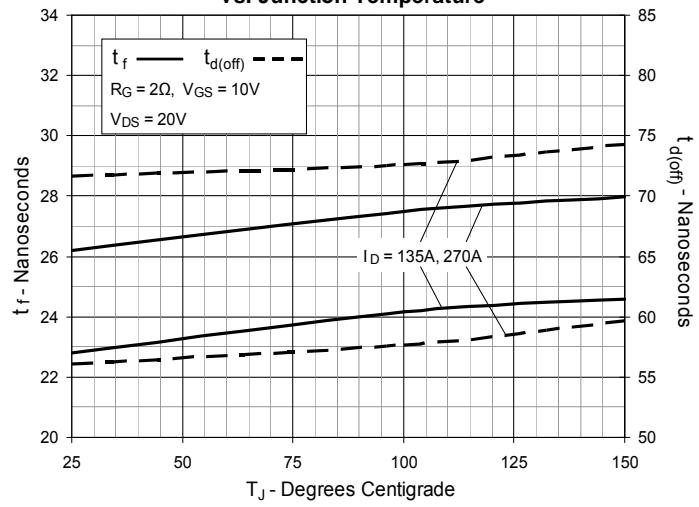


Fig. 17. Resistive Turn-off Switching Times vs. Drain Current

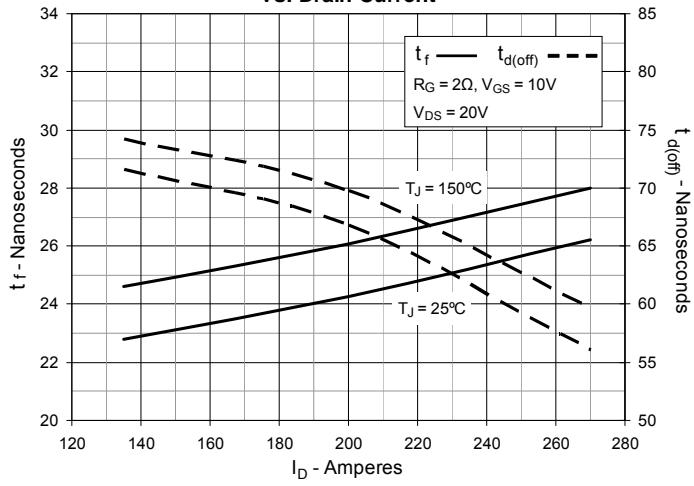


Fig. 18. Resistive Turn-off Switching Times vs. Gate Resistance

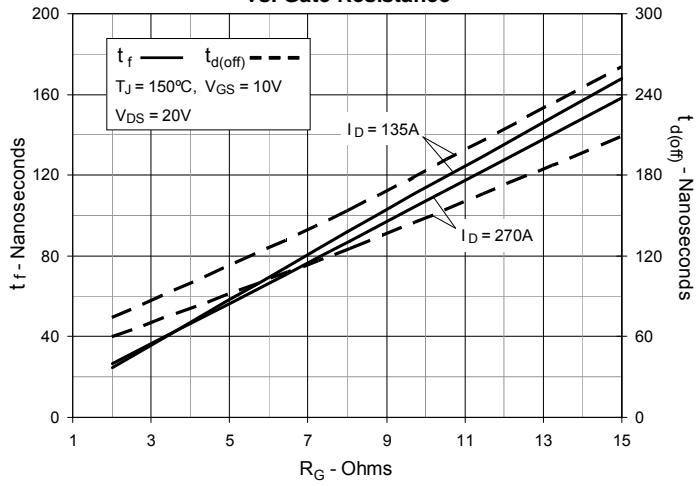
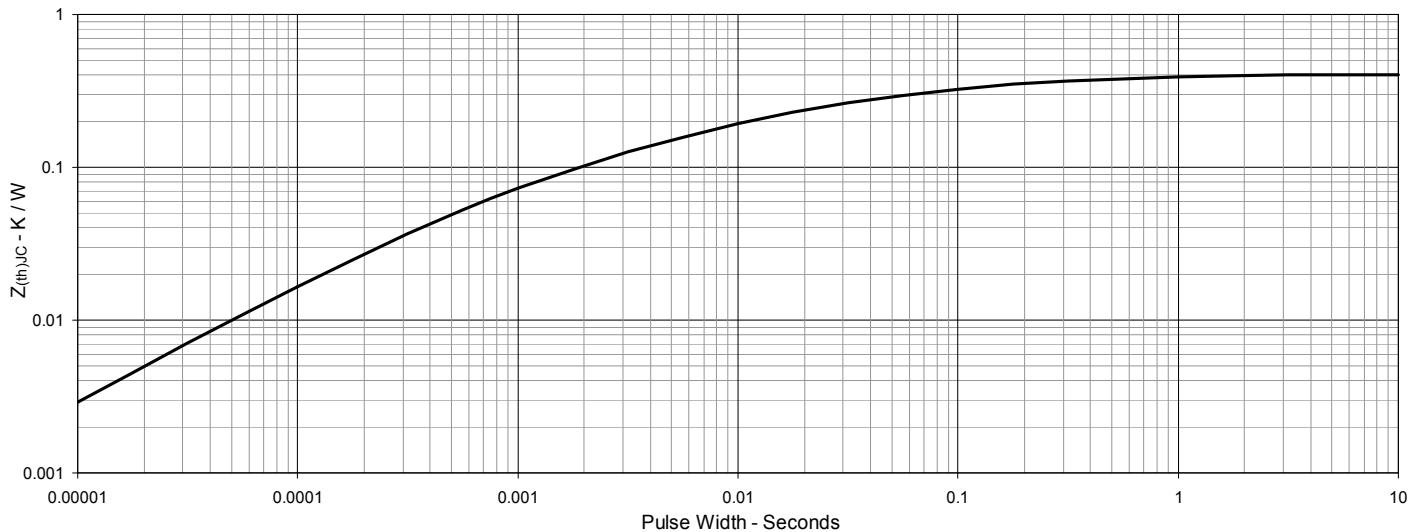
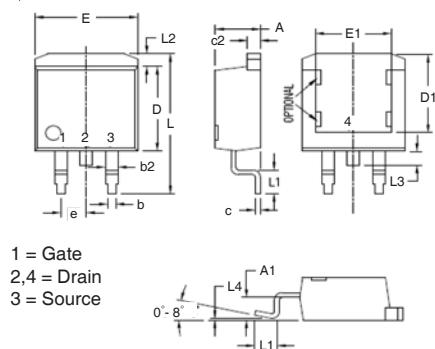
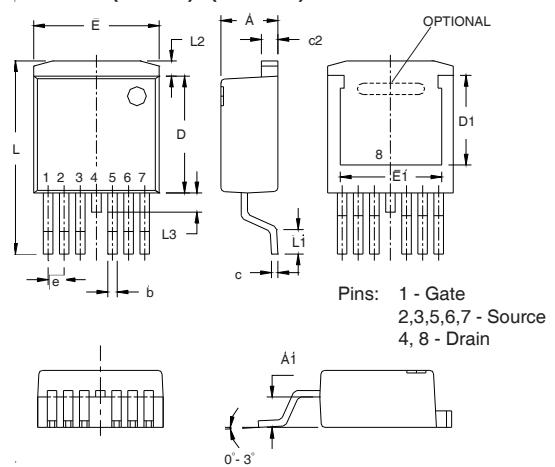


Fig. 19. Maximum Transient Thermal Impedance

**TO-263 (IXTA) Outline**

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.160	.190	4.06	4.83
A1	.080	.110	2.03	2.79
b	.020	.039	0.51	0.99
b2	.045	.055	1.14	1.40
c	.016	.029	0.40	0.74
c2	.045	.055	1.14	1.40
D	.340	.380	8.64	9.65
D1	.315	.350	8.00	8.89
E	.380	.410	9.65	10.41
E1	.245	.320	6.22	8.13
e	.100	BSC	2.54	BSC
L	.575	.625	14.61	15.88
L1	.090	.110	2.29	2.79
L2	.040	.055	1.02	1.40
L3	.050	.070	1.27	1.78
L4	0	.005	0	0.13

TO-263 (7-lead) (IXTA..7) Outline

SYM	INCHES		MILLIMETER	
	MIN	MAX	MIN	MAX
A	.170	.185	4.30	4.70
A1	.085	.104	2.15	2.65
b	.026	.035	0.65	0.90
c	.016	.024	0.40	0.60
c2	.049	.055	1.25	1.40
D	.355	.370	9.00	9.40
D1	.272	.280	6.90	7.10
E	.386	.402	9.80	10.20
E1	.311	.319	7.90	8.10
e	.050	BSC	1.27	BSC
L	.591	.614	15.00	15.60
L1	.091	.110	2.30	2.80
L2	.039	.059	1.00	1.50
L3	.000	.059	0.00	1.50